

ABSTRACT

The bit lines composed of a conductive film containing the tungsten as a principal component are formed inside the side wall spacers formed on the side walls of the wiring grooves. The TiN film having a higher adhesive strength to the silicon oxide than the tungsten is formed on the boundary faces between the bit lines and the side wall spacers, which functions as an adhesive layer that prevents strippings on the boundary faces between the bit lines and the side wall spacers. Thereby, the invention prevents disconnections, even when the width of the wirings having the tungsten as the principal component is fined to $0.1 \mu\text{m}$ or less.

